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SERIAL

APPLICANT

MORIYA, et al.

FILING DATE

## INFORMATION DISCLOSURE STATEMENT **BY APPLICANT**

(Use several sheets if necessary)

## U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date	
AA							
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## FOREIGN PATENT DOCUMENTS

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## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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